

S2000AF

High voltage NPN power transistor for standard definition CRT display

Features

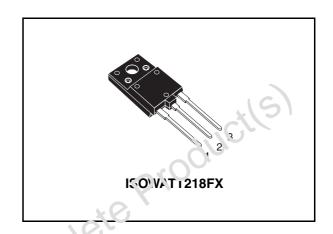
- State-of-the-art technology:
 - Diffused collector "Enhanced generation"
- Stable performances versus operating temperature variation
- Low base-drive requirement
- Tigh h_{FE} range at operating collector current
- High ruggedness
- Fully insulated power package U.L. compliant

Applications

- Horizontal deflection output for CRT TV
- Switch mode power supplies for CRT TV

Description

The S2000AF is manufactured using dinfused collector in planar technology adopting new and enhanced high voltage structure for updated performance to the horizontal deflection stage.



C o (2)

SC06960

Internal schematic diagram

Table 1. Device summary

Order code	Marking	Package	Packaging
S2000AF	S2000AF	ISOWATT218FX	Tube

'-igure 1.

Content S2000AF

Content

1	Electrical ratings 3
2	Electrical characteristics 4
	2.1 Electrical characteristics (curves)
	2.2 Test circuits
3	Package mechanical data 8
4	Revision history
	Obsolete '
	Product(s)
005	Electrical characteristics

S2000AF Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	1500	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	700	V
V _{EBO}	Collector-base voltage (I _C = 0)	9	V
I _C	Collector current	8	Α
I _{CM}	Collector peak current (t _P < 5ms)	15	A
I _B	Base current	4.0	Α
P _{TOT}	Total dissipation at T _c = 25°C	5 0	W
V _{ins}	Insulation withstand voltage (RMS) from all three leads to external heatsink		V
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature 150		

Table 3. Thermal data

	Symbol	Parameter		Value	Unit	
	R _{thj-case}	Thermal resistance junction-case	max	2.5	°C/W	
,so)	eteP	rodulo				
0/050						

S2000AF **Electrical characteristics**

Electrical characteristics 2

(T_{case} = 25°C unless otherwise specified)

Electrical characteristics Table 4.

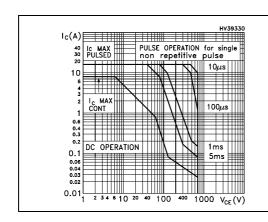
Symbol	Parameter	Test cond	itions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} =0)	V _{CE} = 1500V V _{CE} = 1500V;	T _C = 125°C			0.2 2	mA mA
I _{EBO}	Emitter cut-off current (I _C =0)	V _{EB} = 9V				1 -	mA
V _{CEO(sus)} (1)	Collector-emitter sustaining voltage (I _C =0)	I _C = 100mA		700	40		V
V _{CE(sat)} (1)	Collector-emitter saturation voltage	I _C = 4.5A I _C = 4.5A	I _B = 2A I _B = 1,	10		1 5	V
V _{BE(sat)} (1)	Base-emitter saturation voltage	I _C = 4.5A	1 ₃ = 1A			1.2	V
h _{FE} ⁽¹⁾	DC current gain	$I_C = 1A$ $I_C = 1$	$V_{CE} = 5V$ $V_{CE} = 5V$	10 4.5		30 9	
t _s t _f	Inductive load Storage time Fall time	$I_C = 4.5A$ $I_{BE(off)} = -2.7V$ $I_{BB(off)} = 4.5\mu H$	$B(on) = 0.5A$ $f_h = 16KHz$		2.5 0.2		μs μs
1. Pulsed: Pul	lse duration = 3J0 ms, duty cyc	ele 1.5 %					

^{1.} Pulsed: Pulse duration = 300 ms, duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve



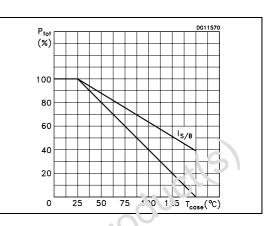
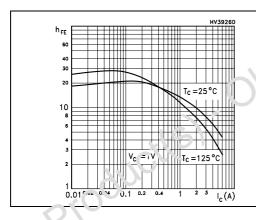


Figure 4. DC current gain

Figure 5. DC ourrent gain



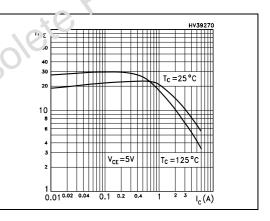
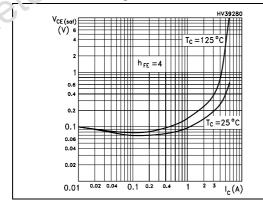
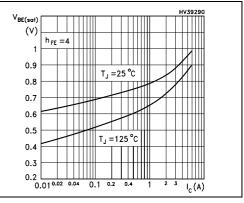


Figure 6. Collector-emitter saturation voltage

Figure 7. Base-emitter saturation voltage

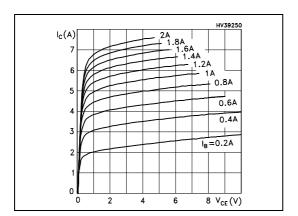




577

Electrical characteristics S2000AF

Figure 8. Output characteristics



Obsolete Productis). Obsolete Productis

2.2 Test circuits

Figure 9. Power losses and inductive load switching

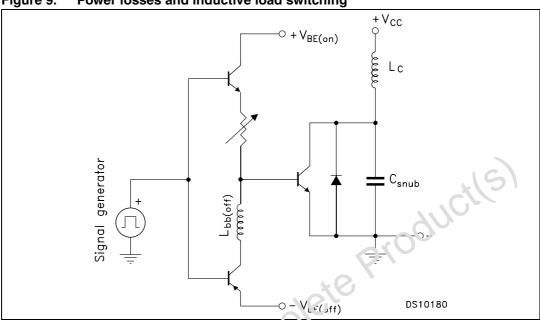
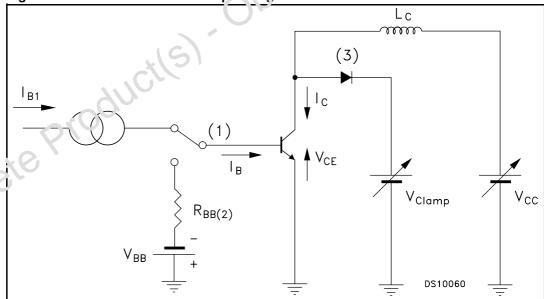


Figure 10. Reverse biased safe operating area



5//

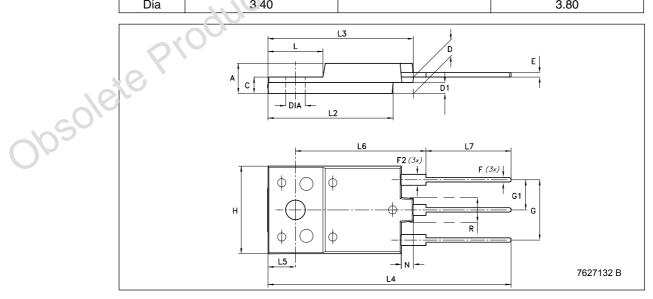
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

Obsolete Producits). Obsolete Producits)

ISOWATT218FX mechanical data

Dim.		mm.		
Dim.	Min.	Тур	Max.	
Α	5.30		5.70	
С	2.80		3.20	
D	3.10		3.50	
D1	1.80		2.20	
E	0.80		1.10	
F	0.65		0.95	
F2	1.80		2.20	
G	10.30		1 .50	
G1		5.45	40,	
Н	15.30		15.70	
L	9		10.20	
L2	22.80	.0.	23.20	
L3	26.30	10,10	26.70	
L4	43.20		44.40	
L5	4.30	-W5	4.70	
L6	24.30		24.70	
L7	14.60		15	
N	1.80		2.20	
R	કે 80		4.20	
Dia	3.40		3.80	



Revision history S2000AF

4 Revision history

Table 5. Document revision history

Date	Revision	Changes
02-Mar-2007	1	Initial release.
14-Aug-2007	2	Complete document, added all curves (2.1: Electrical characteristics (curves)

Obsolete Product(s). Obsolete Product(s)

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its sulhsidia. 'eu ('ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and sen ices described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and solvices described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property Liq. is s granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained in a line in any manner whatsoever of such third party products or services or any intellectual property contained in a line in any manner whatsoever of such third party products or services or any intellectual property contained in a line in any manner whatsoever of such third party products or services or any intellectual property contained in a line in

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE ANCION BALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNE'SE FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN VIRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCT'S OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PF OP ENTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of S. p. or ucts with provisions different from the statements and/or technical features set forth in this document shall immediately void any war and granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liabi. To T.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

577